

Test Beam Results of Highly Irradiated 3D and Planar Pixel Sensors Interconnected to the RD53A Readout Chip

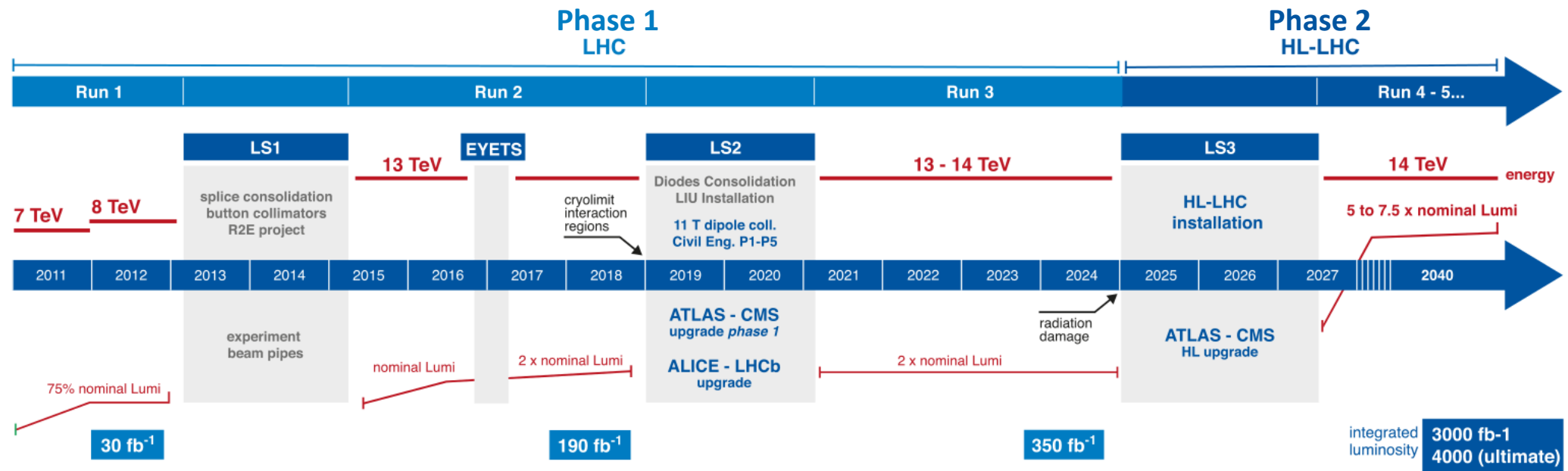
Rudy Ceccarelli

On behalf of the CMS Tracker Group

22/06/2022

High Luminosity LHC

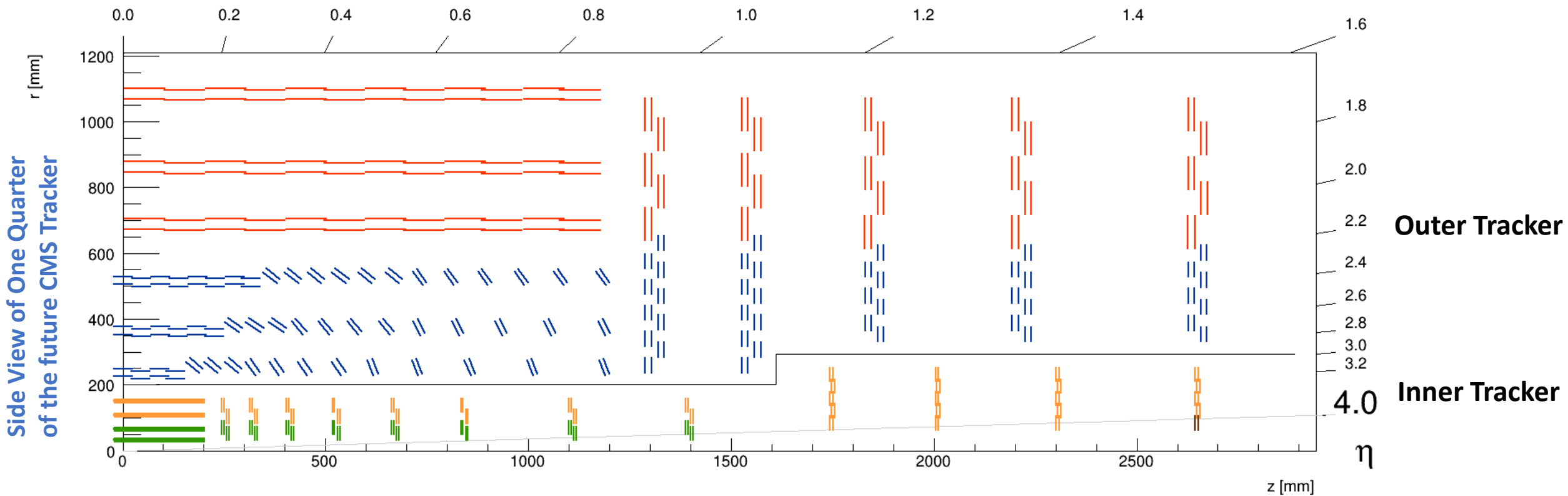
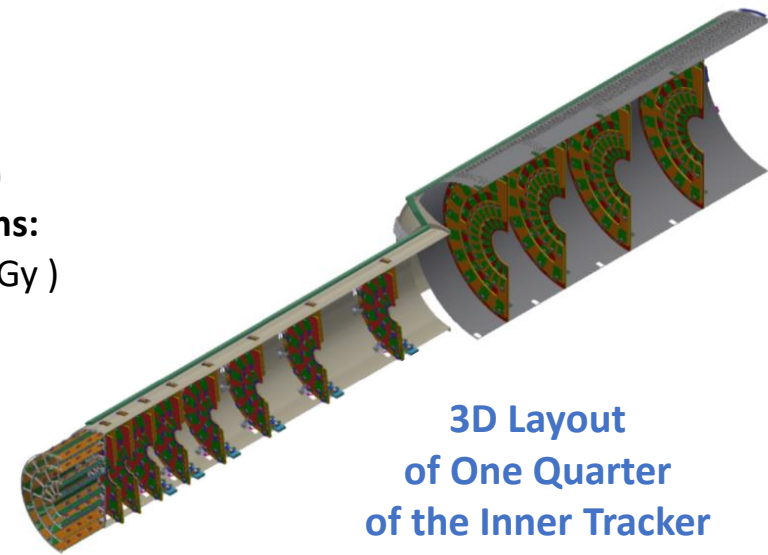
- HL-LHC will be installed between 2025 and 2027 → CMS will restart data taking in 2027 (start of Phase 2)
- Luminosity \mathcal{L} will reach $7.5 \times 10^{34} \text{ cm}^{-2} \text{ s}^{-1}$
- Collect up to $\mathcal{L}_{\text{int}} = 4000 \text{ fb}^{-1}$ in 10 years (to be compared with the expected 500 fb^{-1} at the end of Phase 1)
 - Study rare events of the Standard Model or search for new physics
- All the CMS detectors will be upgraded → Hit rate up to 3.2 GHz cm^{-2}
 - The silicon tracker will be completely replaced



The CMS Tracker Upgrade

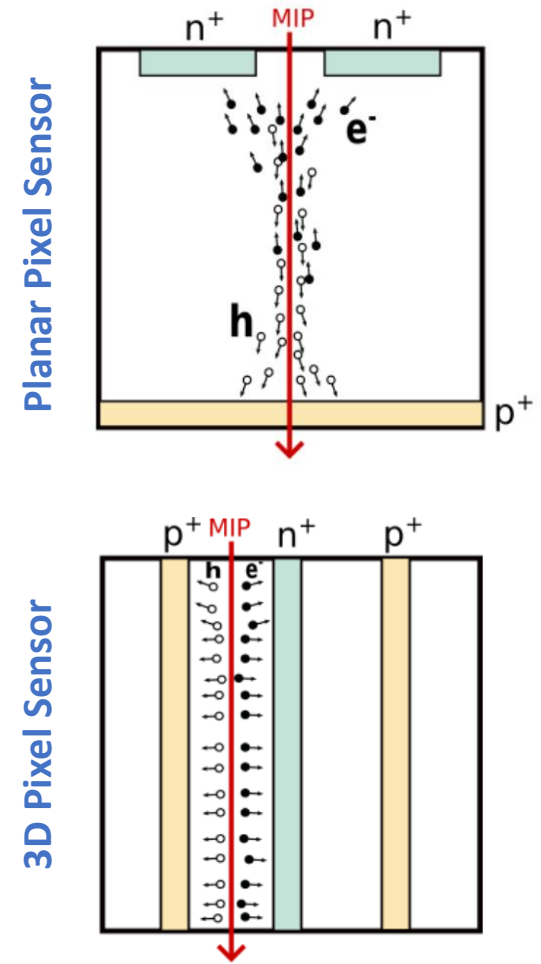
- Composed by two sections:
 - Inner Tracker** → Pixel detectors (this presentation)
 - 4.9 m² of pixel surface and 2×10^9 channels
 - Inner layer at only 30 mm from the beam line
 - Outer Tracker** → Strip and macro-pixel detectors

Expected fluence (dose)
after 10 years of operations:
 $35 \times 10^{15} \text{ n}_{\text{eq}} \text{ cm}^{-2}$ (19 MGy)



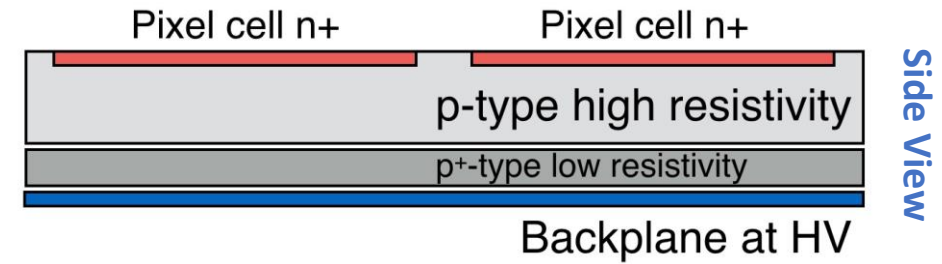
Silicon Pixel Sensors

- Two types of sensors are considered for the new tracker:
 - Standard “planar” pixel sensors
 - **3D** pixel sensors → Higher **radiation resistance**
 - New technology: considered only for the innermost layer
- In 3D sensors the drift path is perpendicular to the active thickness
 - Short drift distance of charge carriers: $\sim 30 - 50 \mu\text{m}$ (vs. $100 - 150 \mu\text{m}$ for planar)
- 3D sensors have many advantages with respect to planar sensors:
 - Smaller bias voltages needed to deplete the sensor
 - Reduced trapping probability in irradiated sensors
- **Active thickness** (for both 3D and planar pixel sensors): $150 \mu\text{m}$
- **Pixel size** (pitch): $50 \times 50 \mu\text{m}^2$ or $25 \times 100 \mu\text{m}^2$ (six times smaller w.r.t. the present CMS tracker)
 - **$25 \times 100 \mu\text{m}^2$** is now the baseline for the whole Inner Tracker

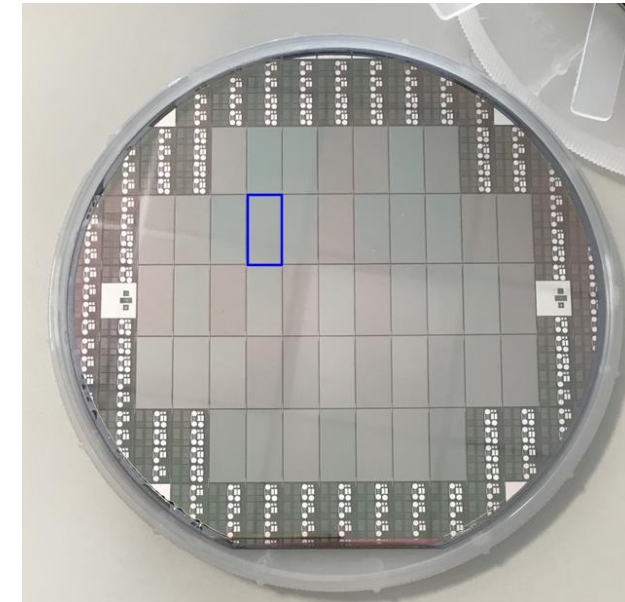


Planar Pixel Sensors

- The planar pixel sensors studied in this presentation are made by:
 - An active area, the substrate (p -doped, high resistivity silicon)
 - Superficial n^+ implants used as collecting **electrodes**
- A low resistivity silicon layer is bonded to the high resistivity substrate (Silicon-Silicon)
 - Mechanical support for the silicon wafer during production
 - Ohmic contact for the $p - n$ junction
 - Thinned and metallized after production → Total sensor thickness around $250\ \mu\text{m}$
 - “Direct Wafer Bonding” (DWB) technique
- The bias voltage is applied to the ohmic contact, on the backside of the sensor

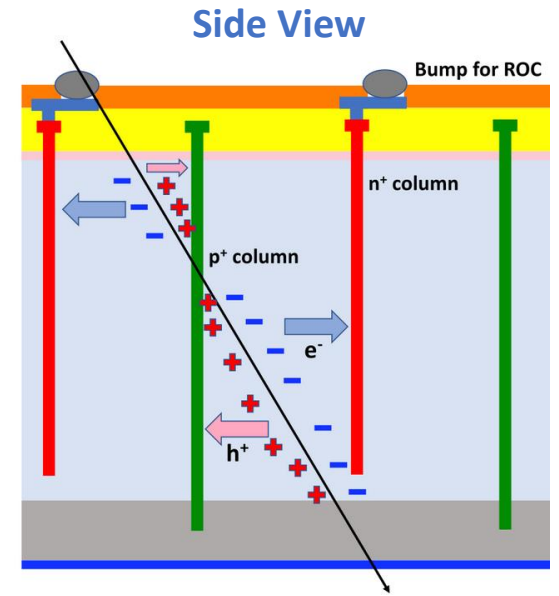


Silicon Wafer

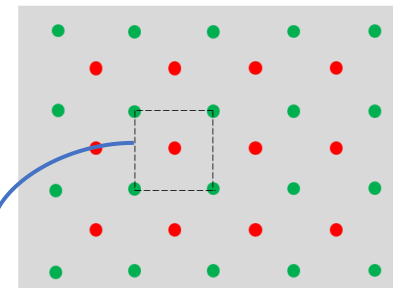
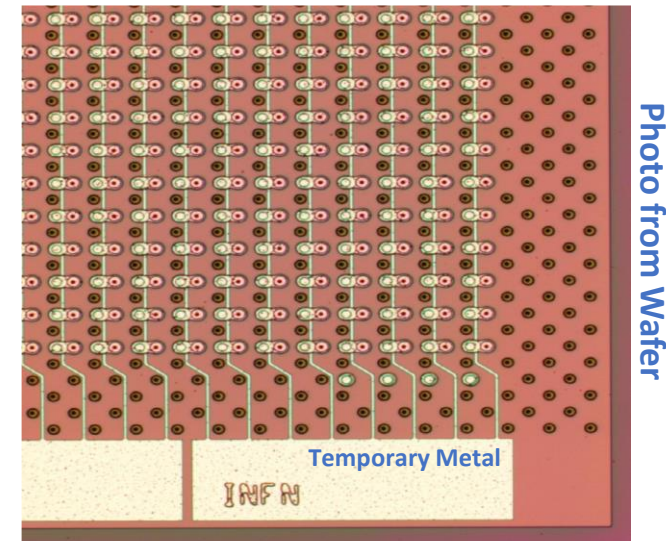


3D Pixel Sensors

- 3D pixel sensors studied in this presentation are fabricated with the DRIE technique
- Columnar implants penetrate deep into the substrate from the same silicon face
 - 5 μm diameter holes in silicon
 - The columns are doped differently: p^+ and n^+
 - p^+ columns reach the backside of the sensor, hence the bias voltage
 - n^+ columns are connected to the readout chip
- A pixel “cell” is delimited by p^+ columns
 - n^+ column in the center of the cell
- Pixel sensors studied in this presentation (planar and 3D) were developed in a collaboration between INFN and FBK foundry (Trento)



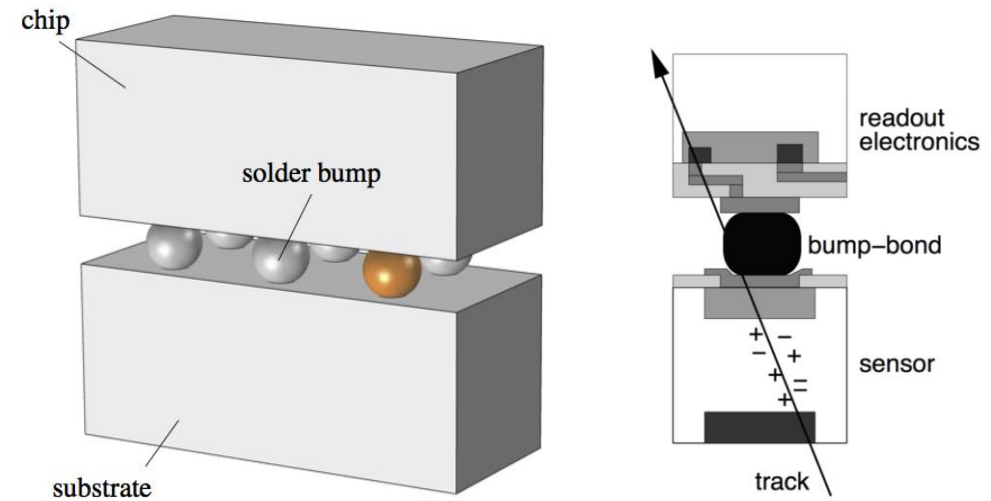
Top Views



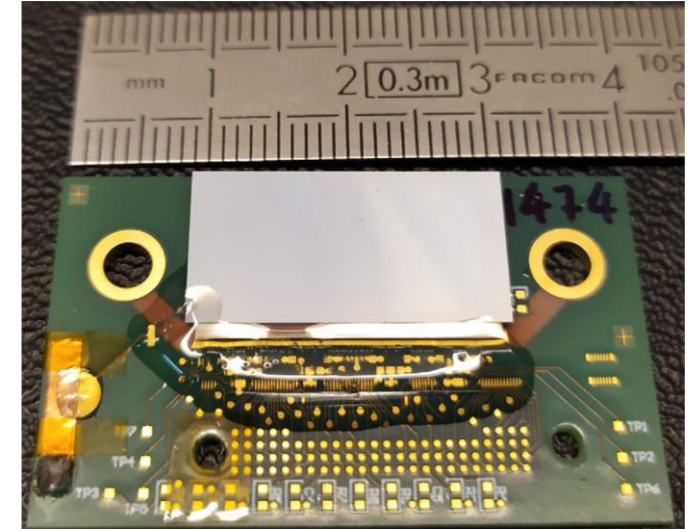
Pixel Cell

The Readout Chip

- The ReadOut Chip (ROC) is coupled to the sensor
 - Bump bonding technique
 - Sensor + ROC → Pixel module
- RD53 chip project (collaboration between ATLAS and CMS)
 - 65 nm technology and $50 \times 50 \mu\text{m}^2$ (single) cell size
 - Radiation hard (certification up to 5 MGy)
- RD53A ($\sim 1/2$ size of the final chip) is the first prototype
 - 76800 pixel channels (only the central zone was readout for this presentation)
 - Used for R&D in the last years
- Various calibrations are needed to operate the pixel modules
 - For instance, the pixels channels can be tuned to average thresholds below 1000 electrons (with a dispersion of ~ 50 electrons) before irradiation



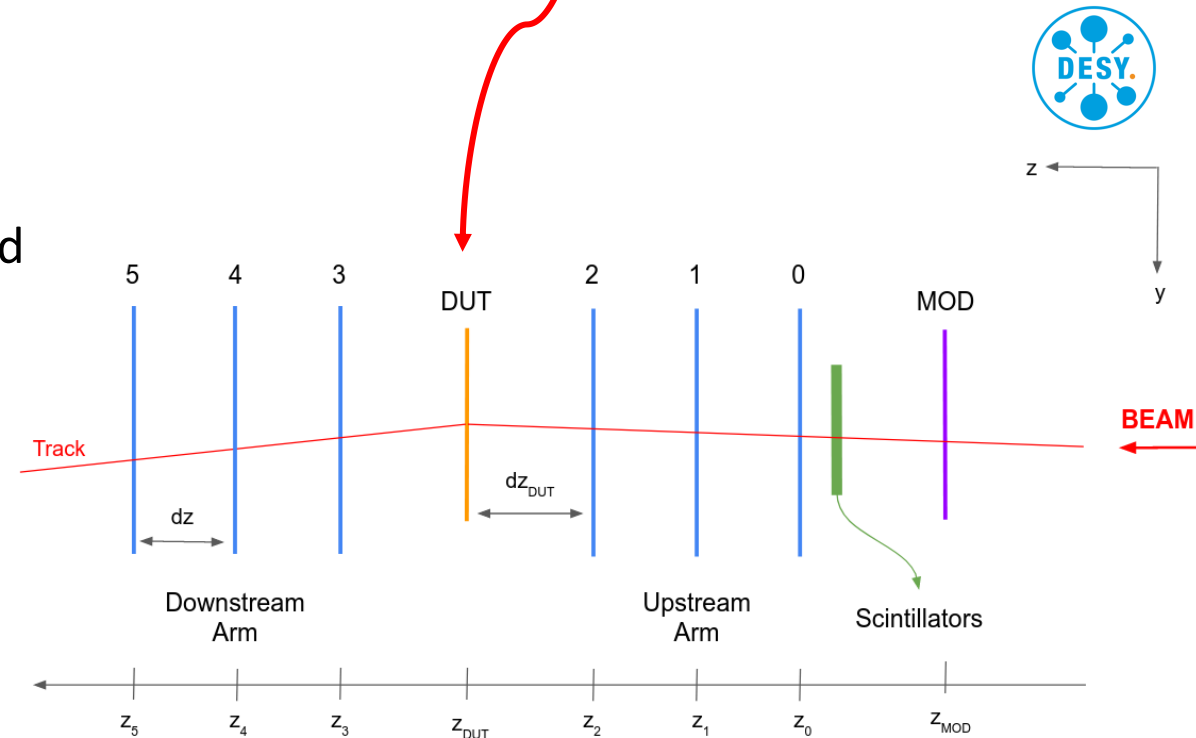
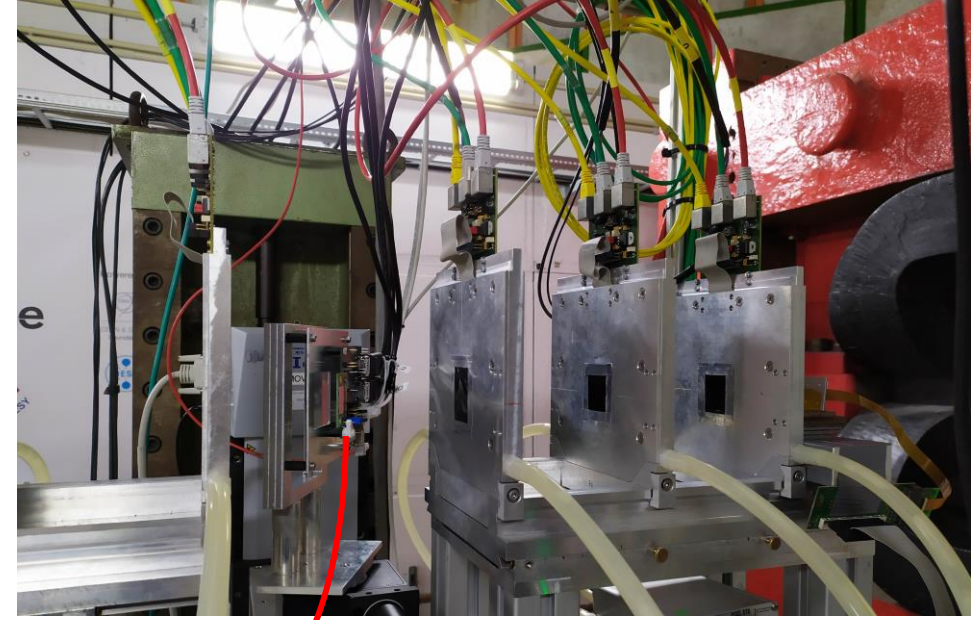
Bump Bonding



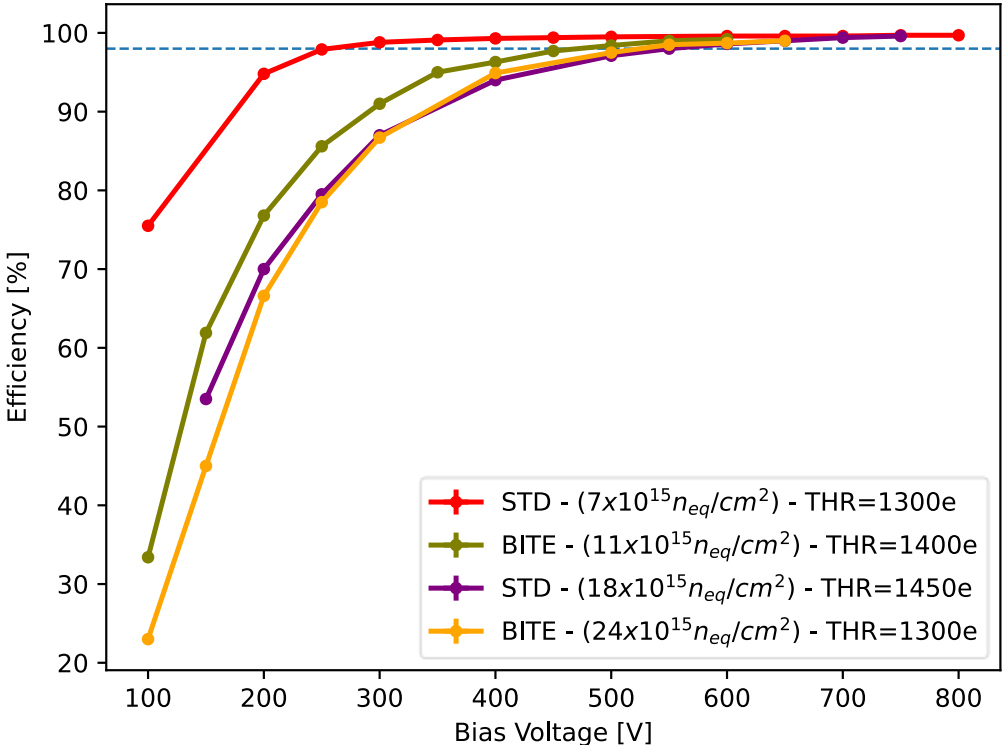
Sensor + RD53A ROC assembly

The DESY Test Beam Facility

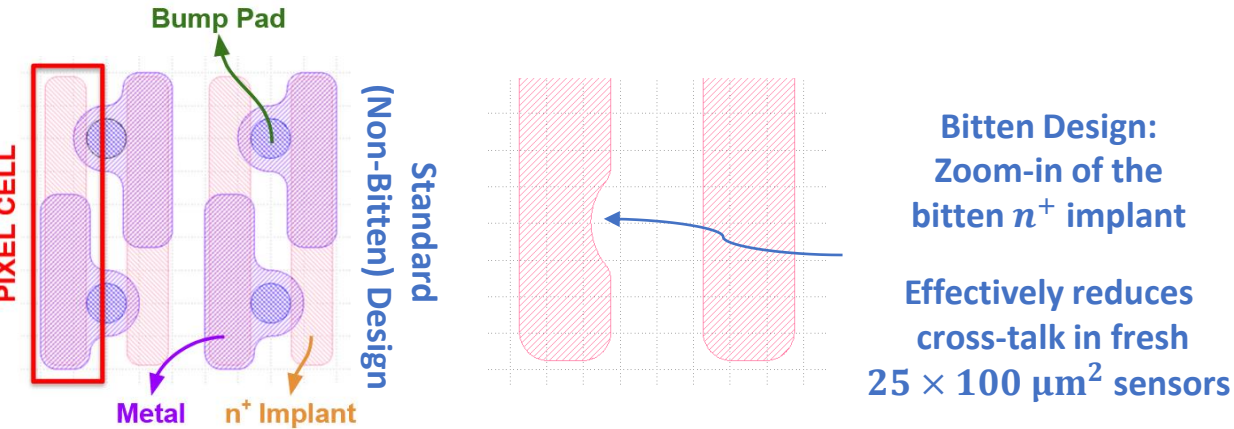
- Several Test Beam experiments at DESY...
 - ...to fully characterize 3D and planar pixel modules
 - Test beam facility (5.2 GeV electron beam)
- **Telescope:** EUDET type (MIMOSA26 pixel sensors)
 - Six planes of tracking detectors
- **DUT:** Device Under Test, our tested pixel module
- Pixel modules are tested before and after being irradiated
 - To fluences equivalent to those expected in HL-LHC
- Irradiated DUTs are kept inside a cooling box
 - Stable temperature of about $-27\text{ }^{\circ}\text{C}$
 - Compensate the effects of radiation damage



Irradiated Planar Pixel Modules – Hit Detection Efficiency

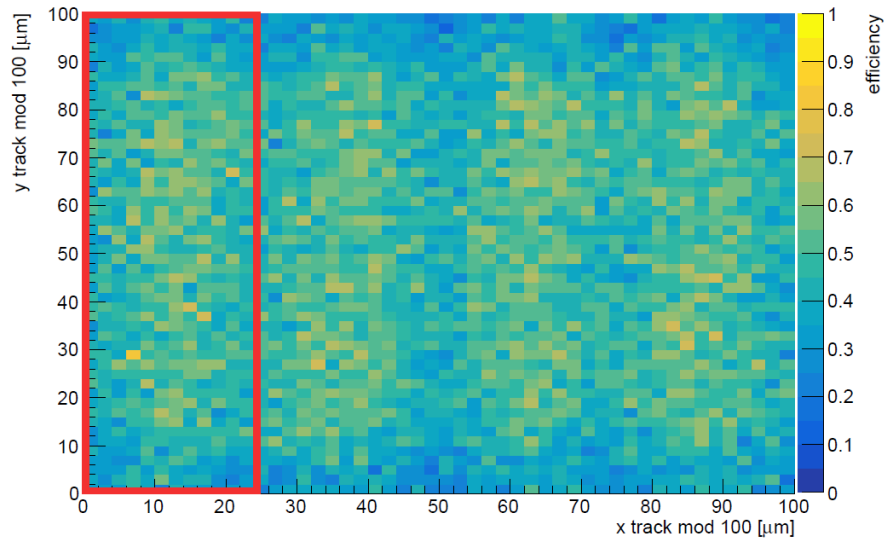


- Four $25 \times 100 \mu\text{m}^2$ **irradiated** planar pixel modules (Standard and Bitten designs) were tested on beam
- Hit detection efficiency vs. the bias voltage
- In order to reach an efficiency $> 98\%$:
 - $V_{\text{bias}} > 400 \text{ V}$ after a fluence of $11 \times 10^{15} \text{ n}_{\text{eq}} \text{ cm}^{-2}$
 - $V_{\text{bias}} > 600 \text{ V}$ after a fluence of $23 \times 10^{15} \text{ n}_{\text{eq}} \text{ cm}^{-2}$
- Planar pixel modules in the innermost tracker layers can survive for more than half the HL-LHC program
 - However, very high bias voltages are required
 - Cooling becomes challenging



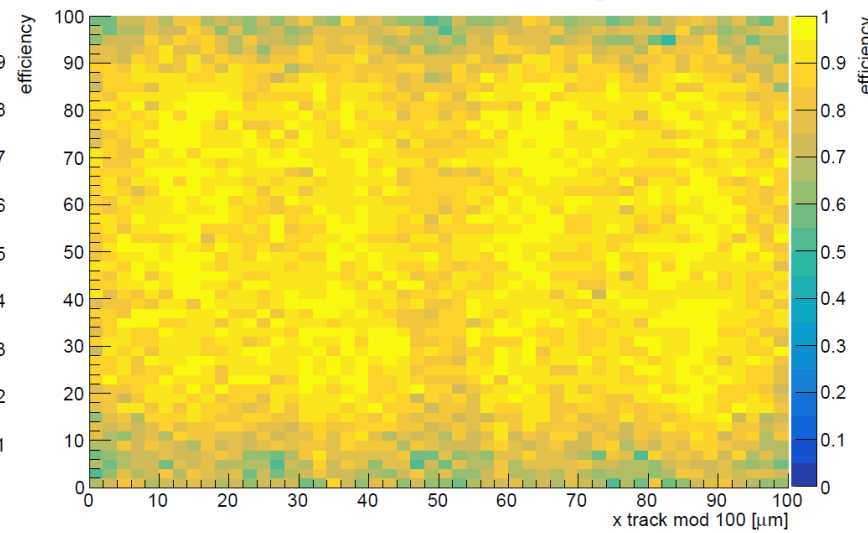
Irradiated Planar Pixel Modules – Hit Detection Efficiency

PIXEL CELL

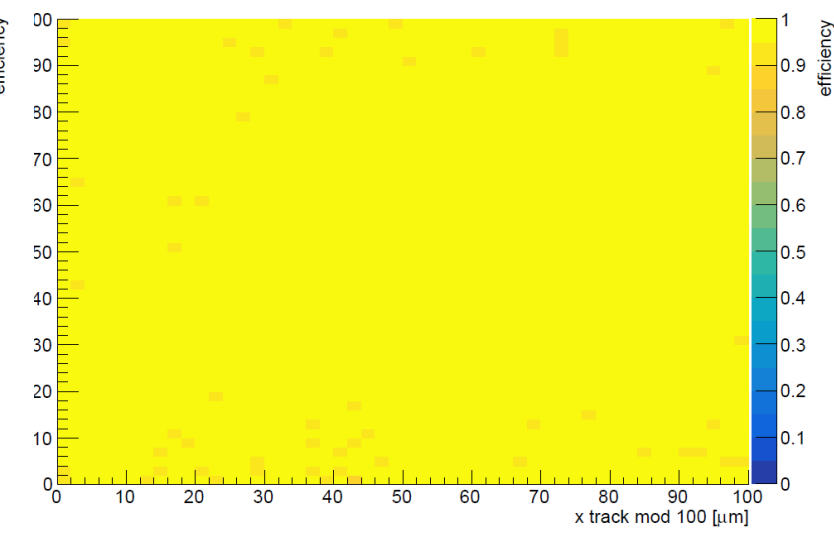


$V_{\text{bias}} = 150 \text{ V}$

BITE - $23 \times 10^{15} \text{ n}_{\text{eq}} \text{ cm}^{-2}$



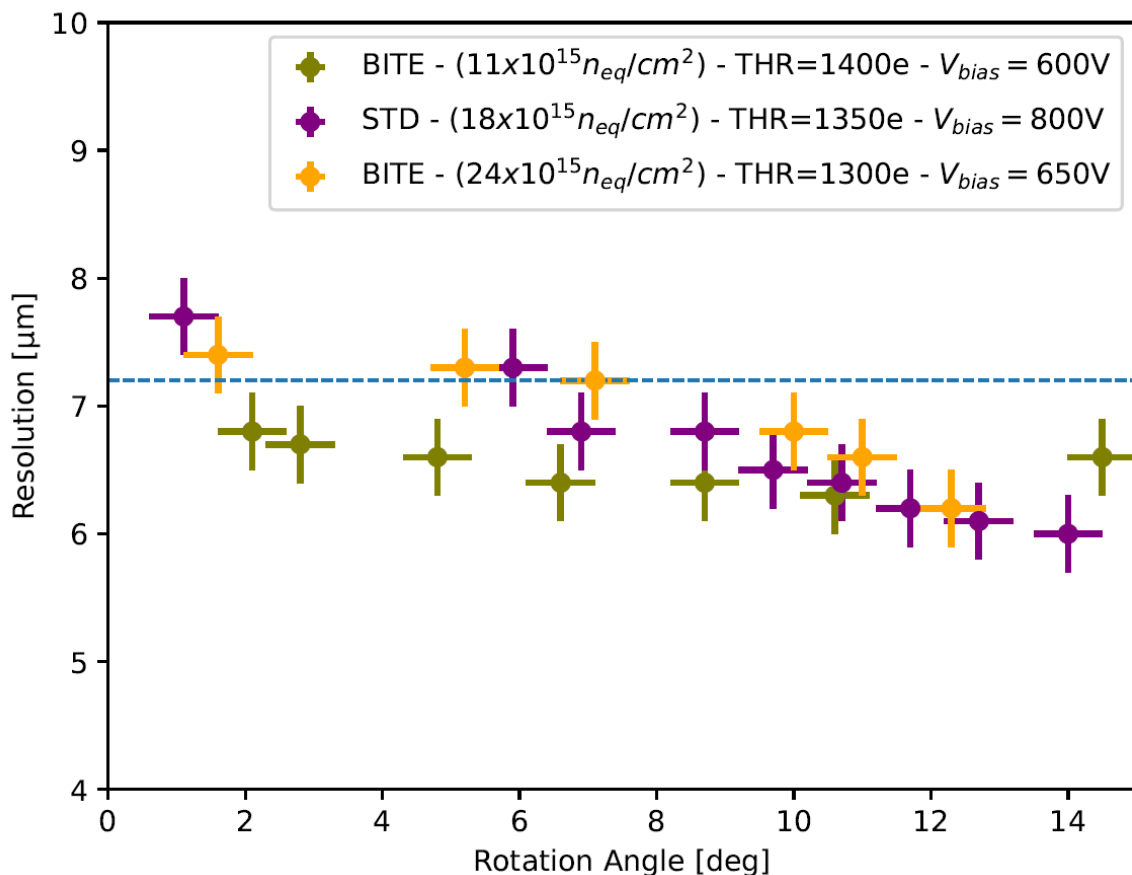
$V_{\text{bias}} = 350 \text{ V}$



$V_{\text{bias}} = 650 \text{ V}$

- Hit detection efficiency map for a 4×1 pixel grid, with increasing V_{bias} and **perpendicular track incidence**
- At low V_{bias} the efficiency is lower at the intersection of adjacent pixels
 - Due to charge sharing between pixels and charge trapping in highly irradiated silicon
- By increasing V_{bias} the efficiency increases and becomes more uniform across the pixel cells
 - More depleted sensor and higher electric field → Higher collected charge and higher detection efficiency

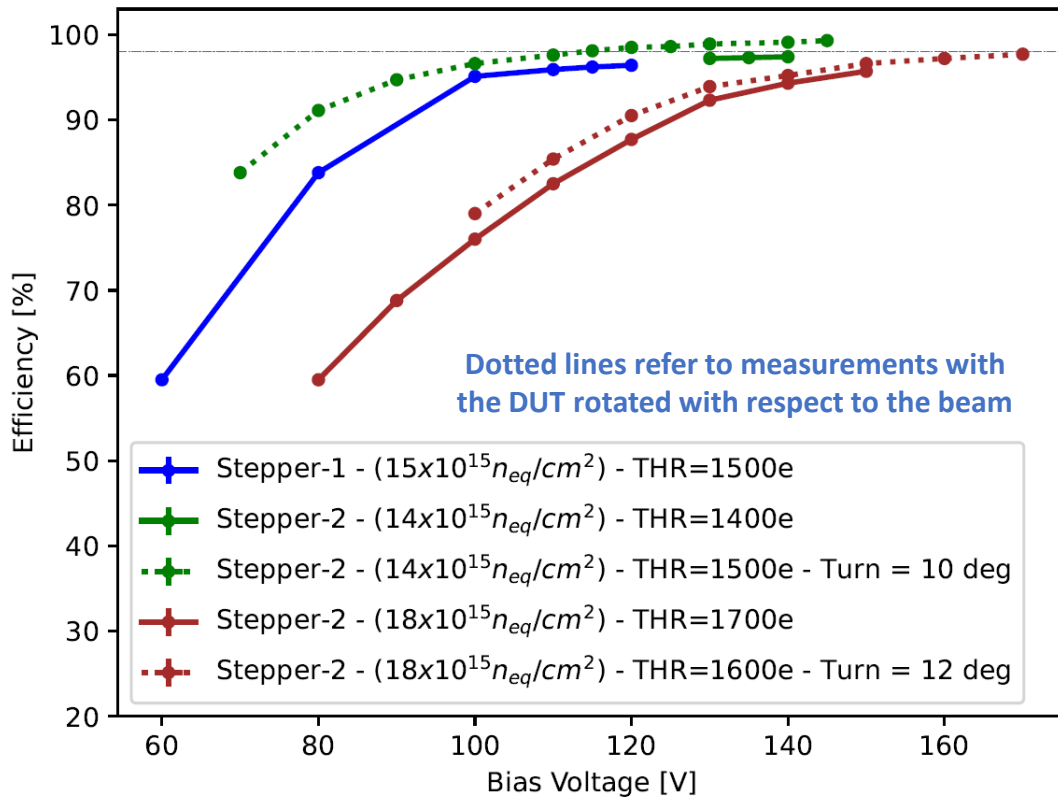
Irradiated Planar Pixel Modules – Resolution



The horizontal line marks the digital resolution

- Resolution vs. rotation angle (w.r.t. the beam)
 - Rotation around the 25 μm pitch
- Due to the presence of the cooling box, only the upstream telescope planes are used in reconstruction
 - Telescope resolution estimated with simulation...
 - ...and subtracted in quadrature
- In fresh modules, resolution is 2 μm at the optimal angle
- In irradiated modules the resolution is deteriorated
 - Due to charge trapping → Lower cluster size
 - However, resolutions close to 6 μm can be achieved
 - Despite the extreme irradiation fluences

Irradiated 3D Pixel Modules – Hit Detection Efficiency



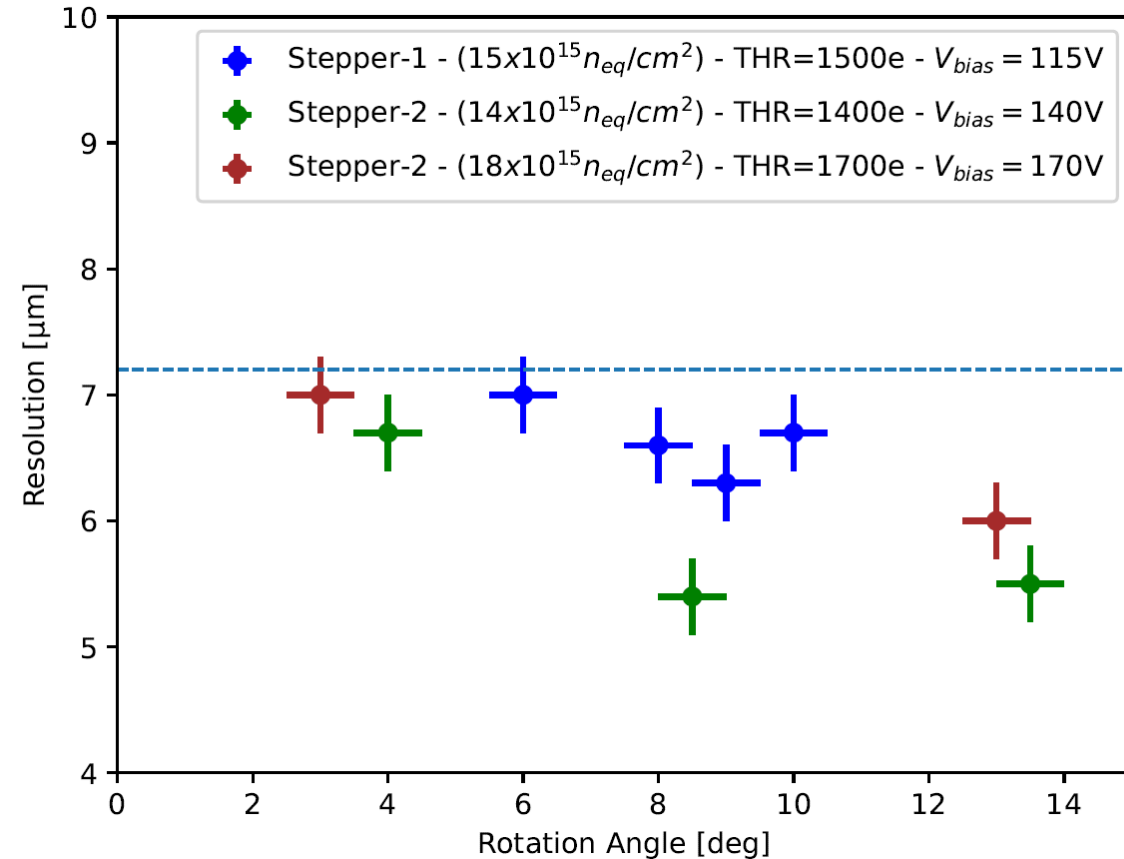
Two FBK 3D productions: **Stepper-1** and **Stepper-2**

(Step-And-Repeat photolithography technology).

The pixel design is the same, but in Stepper-2 the distance between n^+ columns and the backside of the sensor was increased.

- Three $25 \times 100 \mu\text{m}^2$ irradiated 3D pixel modules (Stepper-1 and Stepper-2 productions) were tested on beam
- Hit detection efficiency vs. the bias voltage
- In order to reach an efficiency $> 98\%$:
 - $V_{\text{bias}} > 110 \text{ V}$ after a fluence of $15 \times 10^{15} \text{ n}_{\text{eq}} \text{ cm}^{-2}$
 - $V_{\text{bias}} > 160 \text{ V}$ after a fluence of $18 \times 10^{15} \text{ n}_{\text{eq}} \text{ cm}^{-2}$
- Higher efficiency when the DUT is rotated w.r.t. the beam
 - The columns are made by passive material \rightarrow Inefficiencies
 - By rotating the DUT the inefficiencies are recovered, since incident particles always escape the passive material

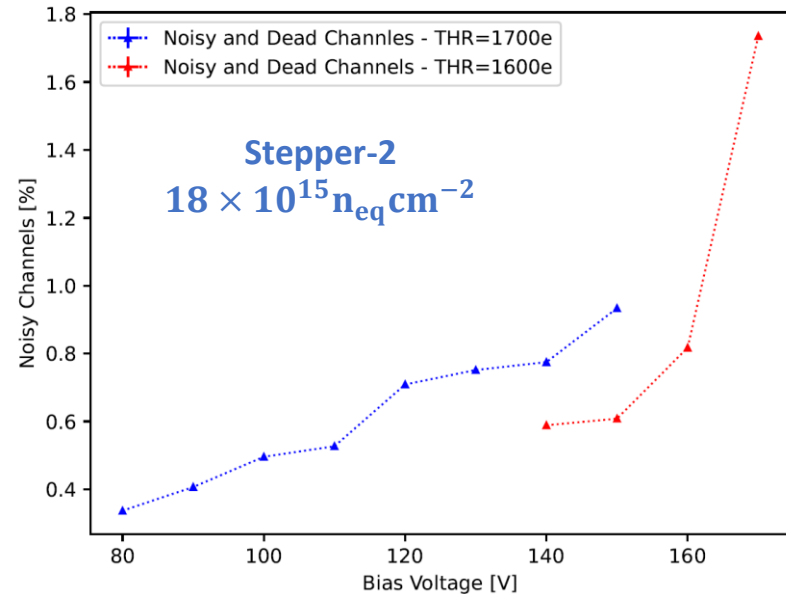
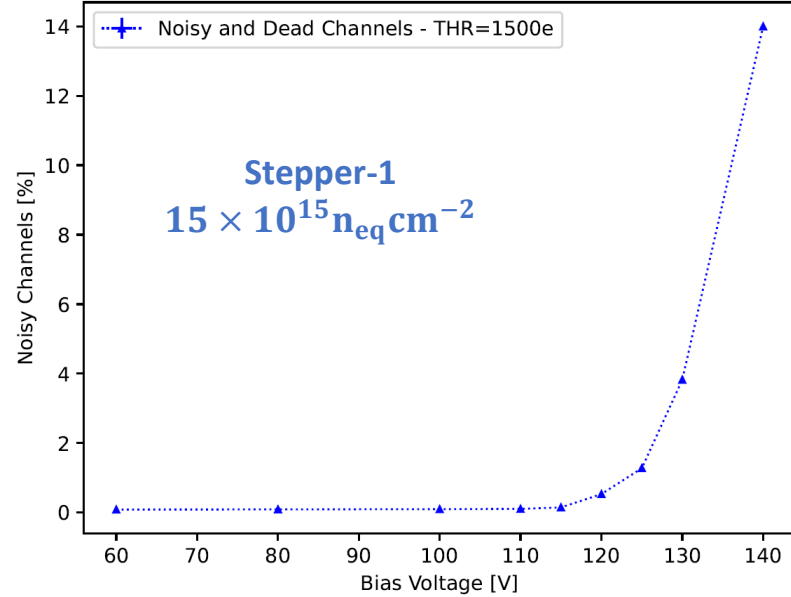
Irradiated 3D Pixel Modules – Resolution



The horizontal line marks the digital resolution

- Resolution vs. rotation angle (w.r.t. the beam)
 - Rotation around the 25 μm pitch
- Telescope resolution is estimated from simulation
- In fresh modules, resolution is 2 μm at the optimal angle
- In irradiated modules the resolution is deteriorated
 - However, resolutions close to 6 μm can be achieved
 - Despite the extreme irradiation fluences
- Compatible results w.r.t. planar pixel modules

Irradiated 3D Pixel Modules – Noisy Channels



- A sudden increase in the number of noisy channels was observed...
 - ...at high bias voltages (greater than 130 – 170 V, depending on the module)
 - The problem was more severe with **Stepper-1** modules (> 10% of channels)
- The cause is still under investigation: might be related to the very high TID
 - The modules were irradiated at KIT with 23 MeV protons
 - The corresponding dose is extremely high: over 30 MGy
 - The RD53A readout chip was design to withstand a maximum of 5 MGy
- New irradiations are currently ongoing at CERN IRRAD facility
 - Up to $20 \times 10^{15} \text{ n}_{\text{eq}} \text{ cm}^{-2}$

Conclusions

- The CMS Inner Tracker project of the HL-LHC is extremely challenging
- Planar pixel modules showed excellent performance after being irradiated to $23 \times 10^{15} \text{ n}_{\text{eq}} \text{ cm}^{-2}$
 - Although with very high bias voltages, $V_{\text{bias}} > 600 \text{ V}$
- 3D pixel modules irradiated to similar fluences showed similar performances
 - With lower bias voltages $V_{\text{bias}} < 200 \text{ V}$
 - The noisy channels behavior is still under study (new modules irradiations with lower TID are ongoing at CERN)
- The presented results will contribute to the optimization of the pixel detectors to be installed in CMS
 - 3D pixel modules will be installed in the innermost layer of the future CMS tracker